

A method for controlling a non-volatile dynamic random access memory provides a non-volatile dynamic random access memory having a storage unit and a control unit. The storage unit has a floating gate for storing charges and a control gate for receiving an operating voltage to determine whether a channel is induced on the surface of a substrate. The channel corresponds to a number of charges stored on the floating gate. A parasitic capacitor exists between the storage unit and the control unit, and a capacitance of the parasitic capacitor increases when the channel has been induced. The method includes applying a first predetermined voltage to the control unit and measuring a voltage variance generated by the parasitic capacitor to analyze data stored by the storage unit.

Figures